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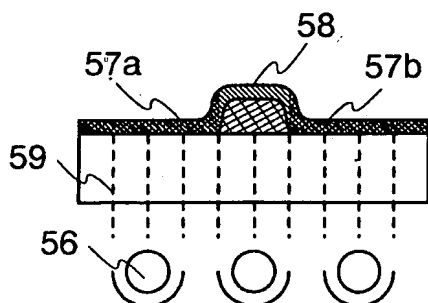
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(54) Title: METHOD FOR FORMING PATTERN, THIN FILM TRANSISTOR, DISPLAY DEVICE AND METHOD FOR MANUFACTURING THE SAME, AND TELEVISION DEVICE



(57) Abstract: A method for forming a pattern according to the invention comprises the steps of: forming a mask over a substrate having light-transmitting properties; forming a first region having a substance including a light-absorbing material over the substrate and the mask; forming a second region by irradiating the substance with light having a wavelength which is absorbable by the light-absorbing material through the substrate to modify a part of the substance surface; and forming a pattern by discharging a compound including a pattern forming material to the second region.